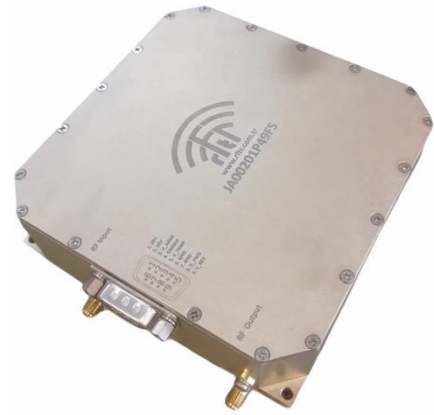


JA0020000P49FS; 20-100 MHz 80W

- Solid-state Class AB design
- Rugged MOS Transistors
- High reliability and ruggedness
- Ultra Broadband
- Temperature and Current Monitorings



ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

Frequency:	20-100 MHz
Output Power:	80 W min. CW
Nominal Gain:	49 dB
Gain Flatness:	± 2.0 dB
Input VSWR:	2:1 max.
Load VSWR for Survival:	∞:1 for 1min.
DC Supply Voltage:	28 V
DC Current:	6.0 A Avg
ON/OFF Switching Time	<6 usec.
Operating Case Temp.:	-40 °C to 85 °C
Storage Temperature:	-40 °C to 85 °C
Shock:	MIL-STD-810F, 516.5
Vibration:	MIL-STD-810F, 514.5

INTERFACES

RF Input:	SMA Female
RF Output:	SMA Female
9 PIN DSUB:	1) 28 V
	2) 28 V
	3) Current
	4) Enable (Active Low)
	5) Temperature
	6) GND
	7) GND
	8) Forward Power
	9) Reverse Power

MECHANICAL SPECIFICATIONS

Size (mm) :	108.6 x 108.6 x 37
Weight :	500 gr.
Plating :	Yellow Chromate

